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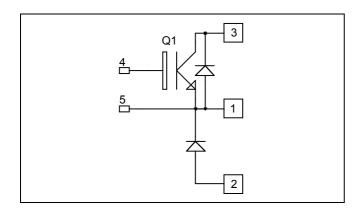
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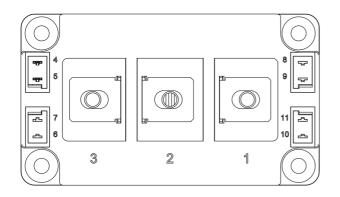
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Buck Chopper Trench + Field Stop IGBT4 Power Module





APTGL475SK120D3G

$V_{CES} = 1200V$ $I_{C} = 475A$ @ Tc = 80°C

Application

- AC and DC motor control
- Switched Mode Power Supplies

Features

- Trench + Field Stop IGBT 4 Technology
 - Low voltage drop
 - Low leakage current
 - Low switching losses
 - Soft recovery parallel diodes
 - Low diode VF
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- High level of integration
- M6 power connectors

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage		1200	V
I _C	Continuous Collector Current	$T_C = 25^{\circ}C$	610	
	Continuous Conector Current	$T_C = 80^{\circ}C$	475	А
I _{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	900	
V_{GE}	Gate – Emitter Voltage		±20	V
P _D	Maximum Power Dissipation	$T_C = 25^{\circ}C$	2080	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	800A @ 1100V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com APTGL475SK120D3G - Rev 1 October 2012



All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics									
Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit			
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				5	mA		
V	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.8	2.2	V		
V _{CE(sat)}	Concetor Emitter saturation voltage	$I_{\rm C} = 400 {\rm A}$ $T_{\rm j} = 125^{\circ} {\rm C}$		2.2		v			
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 15 \text{mA}$		5.0	5.8	6.5	V		
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA		

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$			24.6		
Coes	Output Capacitance				1.62		nF
C _{res}	Reverse Transfer Capacitance				1.38		
Q _G	Gate charge	V _{GE} = -8V / 15V ; V _{CE} =600V I _C =400A			2.3		μC
T _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C)			200		
Tr	Rise Time	$V_{GE} = \pm 15V$			40		
T _{d(off)}	Turn-off Delay Time	$V_{CE} = 600V$ $I_C = 400A$ $R_G = 1\Omega$			400		ns
T _f	Fall Time				70		
T _{d(on)}	Turn-on Delay Time	Inductive Switch	hing (150°C)		220		
T _r	Rise Time	$V_{GE} = \pm 15V$ $V_{CE} = 600V$			50		ns
T _{d(off)}	Turn-off Delay Time	$I_{\rm C} = 400 {\rm A}$	61		500		
T _f	Fall Time	$R_G = 1\Omega$			80		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{CE} = 600V$	$T_J = 150^{\circ}C$		33		mJ
E _{off}	Turn-off Switching Energy	$I_{\rm C} = 400 {\rm A}$ $R_{\rm G} = 1 {\rm \Omega}$	$T_J = 150^{\circ}C$		42		mJ
I _{sc}	Short Circuit data				1600		А

Diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Repetitive Reverse Voltage			1200			V
I _{RRM}	Maximum Reverse Leakage Current	V _R =1200V	$T_j = 25^{\circ}C$ $T_j = 150^{\circ}C$			250 2000	μΑ
I _F	DC Forward Current		$T_C = 80^{\circ}C$		400		А
V _F	Diode Forward Voltage	$I_{\rm F} = 400 {\rm A} \\ V_{\rm GE} = 0 {\rm V}$	$T_j = 25^{\circ}C$		1.7	2.2	V
۴F			$T_{j} = 150^{\circ}C$		1.65		v
t	Reverse Recovery Time	$I_{F} = 400A$ $V_{R} = 600V$ $di/dt = 7000A/\mu s$	$T_j = 25^{\circ}C$		155		ns
t _{rr}			$T_{j} = 150^{\circ}C$		300		
Q _{rr}	$_{\rm T}$ Reverse Recovery Charge $\dot{\rm V}_{\rm R}$		$T_j = 25^{\circ}C$		37.2		μC
Qrr			$T_{j} = 150^{\circ}C$		78		μΟ
E _{rr}	Reverse Recovery Energy		$T_j = 25^{\circ}C$		16		mJ
12m			$T_{j} = 150^{\circ}C$		32		1115

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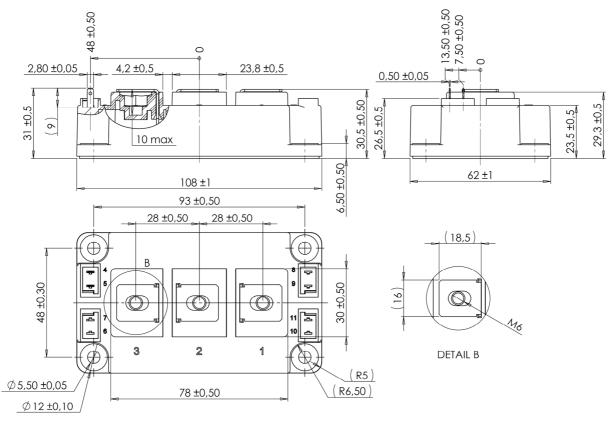


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Thermal and package characteristics

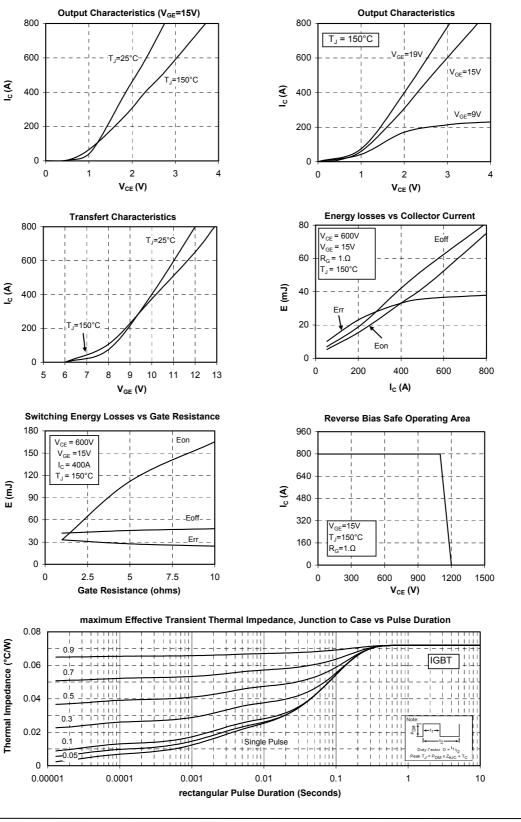
Symbol	Characteristic			Min	Тур	Max	Unit
D	Junction to Case Thermal Resistance		IGBT			0.072	°C/W
R _{thJC} Junction to Case Thermal Resistance			Diode			0.14	C/ W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T _J	Operating junction temperature range			-40		175	
T _{STG}	Storage Temperature Range	Temperature Range -40 125				°C	
T _C	Operating Case Temperature			-40		125	
Torque	Mounting torque	For terminals	M6	3		5	N.m
		To Heatsink	M6	3		5	19.111
Wt	Package Weight					350	g

D3 Package outline (dimensions in mm)





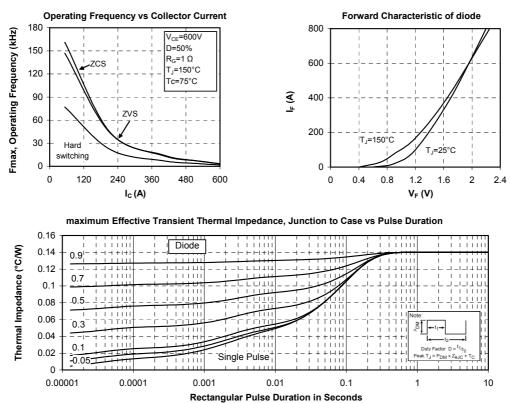
Typical Performance Curve



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